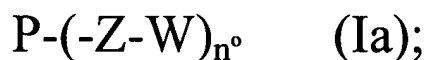


**In the Claims:**

1. (Cancelled).
2. (Currently amended) ~~The dielectric thin film of claim 1,~~ A dielectric thin film prepared by polymerizing an ethylenic-containing precursor with a benzocyclobutane-containing precursor, wherein the ethylenic-containing precursor has a general structure of:



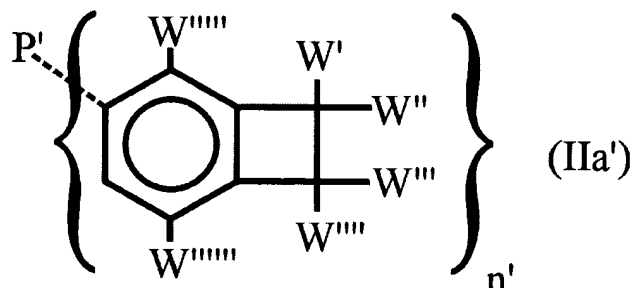
wherein, W is hydrogen, fluorine or a fluorinated phenyl;

P is an aromatic-moiety with a general structure of  $-C_6H_{4-n}F_n-$  ( $n = 0$  to  $4$ );  $-C_6H_4-nF_n-CF_2-C_6H_{4-n}F_n-$  ( $n = 0$  to  $8$ );  $-C_{10}H_{6-n}F_n-$  ( $n = 0$  to  $6$ ), or  $-C_{12}H_{8-n}F_n-$  ( $n = 0$  to  $8$ );

Z is a moiety having an ethylenic group; and

$n^0$  is an integer of ~~at least 2, but is less than total  $sp^2C$  substitutions on the P aromatic moiety;~~

3. (Currently amended) The dielectric thin film of claim 1 2, wherein the benzocyclobutane containing precursor has a general structure of:



wherein, ~~W is~~  $W'$ ,  $W''$ ,  $W'''$ ,  $W''''$ ,  $W'''''$ , and  $W''''''$  are independently the same or different and are hydrogen, fluorine or a fluorinated phenyl;

P' is an aromatic-moiety with a general structure of  $-C_6H_{4-n}F_n-$  ( $n = 0$  to  $4$ );  $-C_6H_4-$   
 $_nF_n-CF_2-C_6H_{4-n}F_n-$  ( $n = 0$  to  $8$  ~~4~~);  $-C_{10}H_{6-n}F_n-$  ( $n = 0$  to  $6$ ), or  $-C_{12}H_{8-n}F_n-$  ( $n = 0$   
to  $8$ ); and

~~n' is an integer of at least 2, but is less than total  $sp^2C$  substitutions on the P' aromatic moiety;~~

4. (Currently amended) The dielectric thin film of claim ~~1~~ 2, wherein the dielectric thin film has a dielectric constant (" $\epsilon$ ") value equal to or less than 2.6.
5. (Currently amended) The dielectric thin film of claim ~~1~~ 2, wherein one or more layers of the thin film is deposited inside an integrated circuit ("IC") or an electronic device.
6. (Original) The dielectric thin film of claim 5, wherein the electronic device comprises an active matrix liquid crystal display, or a fiber optic device.
7. (Original) The dielectric thin film of claim 5, wherein the IC is manufactured via a dual damascene process comprising the dielectric thin film.

Claims 8 – 26. (Withdrawn)